

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **BLV80-28** is Designed for 28 Volt Class C VHF Power Amplifier Applications up to 175 MHz.

FEATURES:

- $\eta_C = 65\%$ min. at 80 W/175 MHz
- $P_G = 6.5$ dB min. at 80 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	9.0 A
V_{CBO}	65 V
V_{CEO}	35 V
P_{DISS}	117 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$1.5^\circ C/W$

PACKAGE STYLE .500 4L FLG

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5.59	.230/5.84
B	.125/3.18	
C	.245/6.22	.255/6.48
D	.720/18.28	.730/18.54
E	.125/3.18	
F	.970/24.64	.980/24.89
G	.495/12.57	.505/12.83
H	.003/0.08	.007/0.18
I	.090/2.29	.110/2.79
J	.160/4.06	.175/4.43
K	.280/7.11	
L	1.050/26.67	

ORDER CODE: ASI10797

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 20$ mA	65			V
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			1.5	mA
h_{FE}	$V_{CE} = 25$ V $I_C = 3.5$ A	15		100	---
C_{OB}	$V_{CB} = 30$ V $f = 1.0$ MHz			150	pF
P_G	$V_{CC} = 25$ V $P_{OUT} = 80$ W $f = 175$ MHz	6.5	7.0		dB
η_C		65			%